

MAR 13 2008

Customer No.: 31561
Docket No.: 12739-US-PA
Application No.: 10/710,698

AMENDMENTS

Please amend the application as indicated hereafter.

To the Title:

Please amend the title filed on November 14, 2007 as follows,

PHYSICAL VAPOR DEPOSITION PROCESS AND APPARATUS THEREFOR

~~FOR PHYSICAL VAPOR DEPOSITION.~~

Customer No.: 31561
Docket No.: 12739-US-PA
Application No.: 10/710,698

To the Specification:

Please replace originally-filed paragraphs [0038], [0044], [0047], [0051] and [0055] with the following amended paragraphs, respectively.

[0038] Referring to FIG. 2A, the wafer 212 is disposed on the platen 204 in the chamber 200 for depositing the thin film on the surface of the wafer 212. FIG. 3A shows the cross-sectional view of the PVD process to form the thin film in the opening of the alignment mark or the overlap mark on the wafer in accordance with the first embodiment of the present invention. The alignment mark or the overlap mark includes the Si-substrate 300 and the dielectric layer 302 on the substrate 300, and the dielectric layer 302 has an opening 304 therein.

[0044] Referring to FIG. 5, the PVD apparatus includes a reaction chamber 203 and a rotating magnetron device 500. The reaction chamber 203 includes the chamber 200, the target backboard 202, the platen 204, the power supply 206, the cover mask 208 and the gas supply device 210. The locations of the elements are the same as those in the first embodiment and thus will not be described again.

[0047] Referring to FIG. 5, first the wafer 212 is disposed on the platen 204 in the chamber 200 for depositing the thin film on the surface of the wafer 212. FIG. [3]6A shows the cross-sectional view of the PVD process to form the thin film in the opening of the alignment mark or the overlap mark on the wafer in accordance with the first

Customer No.: 31561
Docket No.: 12739-US-PA
Application No.: 10/710,698

embodiment of the present invention. The alignment mark includes the Si-substrate 300 and the dielectric layer 302 on the substrate 300, and the dielectric layer 302 has an opening 304 therein.

[0051] Referring to FIG. 7A, the PVD apparatus includes the reaction chamber 203 and a rotating magnetron device 700. The reaction chamber 203 includes the chamber 200, the target backboard 202, the platen 204, the power supply 206, the cover mask 208 and the gas supply device 210. The locations of the elements are the same as those in the first embodiment and thus will not be described again.

[0055] Referring to FIG. 7A, first the wafer 212 is disposed on the platen 204 in the chamber 200 for depositing the thin film on the surface of the wafer 212. FIG. 8A shows the cross-sectional view of the PVD process for forming the thin film in the opening of the alignment mark or the overlap mark on the wafer in accordance with the first embodiment of the present invention. The alignment mark or the overlap mark includes the Si-substrate 300 and the dielectric layer 302 on the substrate 300, and the dielectric layer 302 has an opening 304 therein.